

BIRLA INSTITUTE OF TECHNOLOGY, MESRA, RANCHI
(MID SEMESTER EXAMINATION)

CLASS: BTECH
BRANCH: ECE

SEMESTER: V
SESSION: MO/24

SUBJECT: EC319 VLSI SYSTEMS

TIME: 2:00 Hrs

FULL MARKS: 25

INSTRUCTIONS:

1. The question paper contains 5 questions each of 5 marks and total 25 marks.
2. Attempt all questions.
3. The missing data, if any, may be assumed suitably.
4. Before attempting the question paper, be sure that you have got the correct question paper.
5. Tables/Data handbook/Graph paper etc. to be supplied to the candidates in the examination hall.

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|--|-----|----|-----|
| Q.1(a) The data sheet of a CMOS inverter specifies the following parameters: $V_{IHmin} = 700$ mV, $V_{OHmin} = 900$ mV, $V_{ILmax} = 300$ mV, $V_{OLmax} = 100$ mV. Calculate the HIGH-state noise margin (NM_H) and the LOW-state noise margin (NM_L). | [2] | 1 | 3 |
| Q.1(b) Describe the switching threshold (V_M) of a CMOS inverter. Explain how its value is obtained graphically. What is the desired value of V_M for a CMOS inverter in $0.25 \mu\text{m}$ process? | [3] | 1 | 2 |
| Q.2(a) Write down the (V_{OL}) and (V_{OH}) of the low swing driver shown in the Figure below. Explain why the output voltage swing (V_{out}) is not rail-to-rail. Assume $\lambda=0$. | [2] | 1 | 2,3 |
| | | | |
| Q.2(b) Write down various regions of operation of MOSFETs and their current equations. Explain the channel length modulation (CLM) effect with a suitable diagram. | [3] | 1 | 2,3 |
| Q.3(a) Deduce the expression of energy E_{VDD} , taken from V_{DD} during the $0 \rightarrow 1$ transition of the output node. | [2] | 1 | 4 |
| Q.3(b) Briefly explain the power-delay product (PDP). Calculate the power-delay product (PDP) of a CMOS inverter designed in a generic $0.25\text{-}\mu\text{m}$ CMOS process having a load capacitance C_L of 6 fF. | [3] | 2 | 3 |
| Q.4(a) What is an Interconnect? Define its pitch and aspect ratio. Substantiate your answer with a suitable diagram of the interconnect. | [2] | 2 | 1 |
| Q.4(b) Define crosstalk (clock feedthrough)? Consider that a clock wire and a victim wire are routed side-by-side. What impact is found on the victim wire if the clock in the clock wire makes a high-to-low transition? Substantiate your answer with a suitable diagram and explain it. | [3] | 2 | 1 |
| Q.5(a) What is skin effect and skin depth? Formulate skin depth mentioning each term in minimum words. | [2] | 2 | 6 |
| Q.5(b) Calculate the skin depth (δ) of aluminum wire ($\rho=2.7 \times 10^{-8} \Omega \cdot \text{m}$) routed through a surrounding dielectric with the permeability of free space (i.e., $\mu = 4\pi \times 10^{-7} \text{ H/m}$) while carrying a current at 1 GHz. | [3] | 2 | 4 |